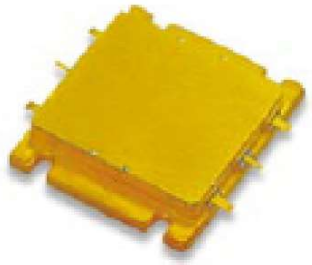
Performance

- Frequency: 2.7-3.5GHz
- Pout: 57dBm @ 48V
- PAE: 55% (typ.)
- Power Gain: 13dB
- Bias: VD=50V, VG=-1.0~-3.0V (typ.)
- Size: 30.8*27.4*6.0mm



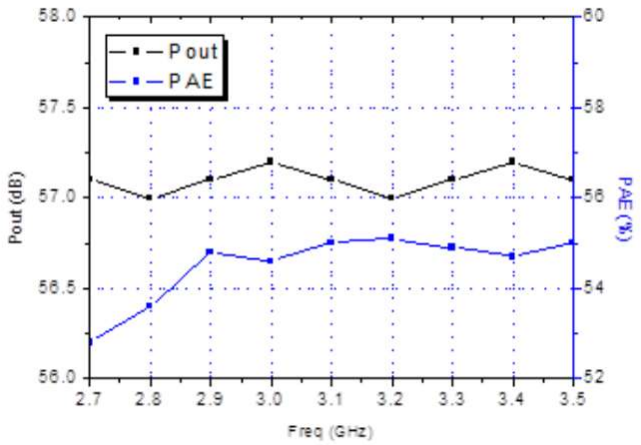
Electrical Specifications (VD=50V, ID≈0.1A, F=2.7~3.5GHz, Pulsed 500us, 15% D.C.)

Symbol	Parameter	Min	Typical	Max	Unit
Gp	Large Signal Gain @ PIN=44dBm	-	13	-	dB
Psat	Saturated Power @ PIN=44dBm	-	57	-	dB
PAE	Power Added Efficiency	-	55	-	%
△Gp	Gain Flatness	-0.3	-	+0.3	dB

Test Curves

(Conditions unless otherwise specified: VD = 50V; ID≈0.1A, F=2.7~3.5 GHz; PIN=44 dBm; Pulsed Wave, 500us, 15% D.C)

Saturated Power, PAE VS. Frequency

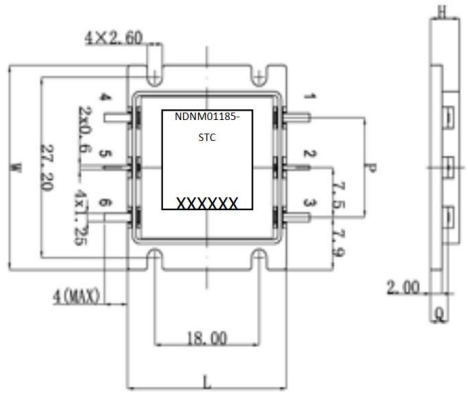


Absolute Max Ratings (TA=25℃)

Symbol	Parameter	Value	Remark
VD	Drain Voltage	80V	
VG	Gate Voltage	-5V	
PD	DC Power	150W	
TCH	Channel Temperature	225℃	
TM	Mounting Temperature	310℃	1min, N2 protection
TSTG	Storage Temperature	-55~175℃	

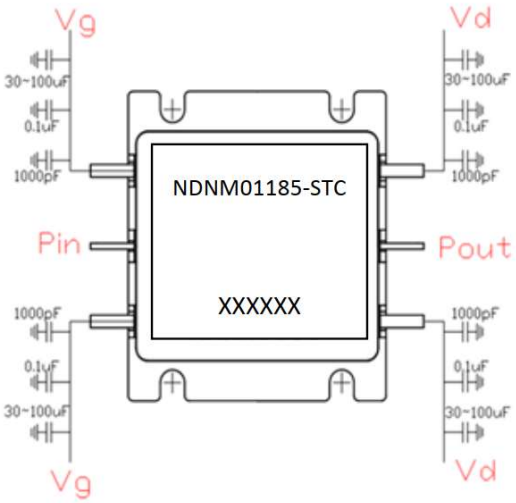
Exceeding any one or combination of these limits may cause permanent damage.

Outline Size



Pin Number	Description
1,3	Vgs
4,6	Vds
2	RFin
5	RFout

Application Circuit



Bias-up Procedure

1 Apply V_G=-1.0~-3.0V(typ.)
2 Apply +50V to V_D
3 Apply pulse signal generator
4 Turn on RF supply

Bias-down Procedure

1 Turn off RF supply
2 Turn off pulse signal generator
3 Turn off V_D supply
4 Turn off V_G supply